Amendments to the Claims

This listing of claims will replace all prior versions, and listings, of claims in the application.

1-20. (Canceled).

21. (Previously Presented) A current switch comprising:

a first means for normally not conducting current and for maintaining conduction of a current in response to a first bias voltage; and

a second means for starting conduction of said current in said first means in response to said first bias voltage.

22. (Previously Presented) The current switch according to Claim 21, wherein said first means comprises a switching device having a first lead for receiving said first bias voltage, a second lead and a third lead, wherein said current is conducted between said second lead and said third lead when said maintaining conduction.

23. (Previously Presented) The current switch according to Claim 22, wherein said second means comprises a starter device having a fourth lead for receiving said first bias voltage, a fifth lead coupled to said second lead of said switching device and a sixth lead coupled to said third lead of said switching device.

24. (Previously Presented) The current switch according to Claim 23, wherein said current is conducted between said fifth lead and said sixth lead when said starting conduction.

25. (Previously Presented) A circuit comprising:

a switching device normally in an off state; and

a starter device for reducing a terminal voltage of said switching device.

26. (Previously Presented) The circuit of Claim 25, wherein said starter device reduces said terminal voltage of said switching device below 0.4 volts.

27. (Previously Presented) The circuit of Claim 26, wherein said reducing said terminal voltage allows said switching device to transition from said off state to said on state.

28. (Previously Presented) The circuit of Claim 25, wherein said switching device is selected from the group consisting of a junction field effect transistor (JFET), a symmetrical junction field effect transistor, an asymmetrical junction field effect transistor, a metal-semiconductor field effect transistor (MESFET).

29. (Previously Presented) The circuit of Claim 25, wherein said starter device is selected from the group consisting of a bipolar junction transistor (BJT), a plurality of bipolar

junction transistors, a metal-oxide-semiconductor field effect transistor (MOSFET), a plurality of metal-oxide-semiconductor field effect transistors, a junction field effect transistor (JFET) and a plurality of junction field effect transistors.

30. (Previously Presented) The circuit of Claim 25, wherein said switching device and said starter device are fabricated on a single substrate.

31. (Previously Presented) An amplifier comprising:

a normally off active device; and

a starter device coupled to said normally off active device for biasing said normally off active device to operate as an amplifier.

32. (Previously Presented) The amplifier of Claim 31, wherein said normally off active device and said starter device are fabricated on a single substrate.

33. (Previously Presented) The circuit of Claim 31, wherein said normally off active device is selected from the group consisting of a junction field effect transistor (JFET), a symmetrical junction field effect transistor, an asymmetrical junction field effect transistor, a metal-semiconductor field effect transistor (MESFET).

34. (Previously Presented) The amplifier of Claim 33, wherein said starter device comprises a bipolar junction transistor (BJT).

35. (Previously Presented) The amplifier of Claim 34, wherein said normally off active device operates as an amplifier when a base to emitter bias voltage of said bipolar junction transistor is approximately 0.4 or more.

36. (Previously Presented) The amplifier of Claim 34, wherein said bipolar junction transistor is parasitic to said normally off active device.

37. (Previously Presented) The amplifier of Claim 33, wherein said starter device comprises a metal-oxide-semiconductor field effect transistor (MOSFET).

38. (Previously Presented) The amplifier of Claim 37, wherein said normally off active device operates as an amplifier when a gate to drain bias voltage of said metal-oxide-semiconductor field effect transistor is approximately 0.4 or more.

39. (Previously Presented) The amplifier of Claim 33, wherein said starter device comprises a plurality of junction field effect transistors (JFET).

40. (Previously Presented) The amplifier of Claim 39, wherein said normally off active device operates as an amplifier when a gate to drain bias voltage of said metal-oxide-semiconductor field effect transistor is approximately 0.4 or more.